

Specification

Project Code: 3S503-V01

Product:1135nm 9mil-3E



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Specification

The specification applies to GaAs infrared chip for 1135nm wavelength range.

The <u>3S503-V01</u> is a <u>1135</u>nm <u>9</u> mil Vertical Cavity Surface Emitting Laser (VCSEL) chip. The product characterized by the IR light wavelength and unique oxide-confined process of VCSELs.

Part Number: VSB36C09000-R001

Features

Wavelength: 1135nm

Chip size: 235 x 235 ± 15 μm
Chip thickness : 150 ± 15 μm

Drive current : 40mA

Output power : 20mW @20μs, Duty 50%

Electrode side : Gold alloy on both anode
P(emission side) and cathode N(backside)

Other configurations available on request

Applications

- Moving sensor/ Gesture
- Optical encoders
- 3D sensing
- Health or medical product
- Mobile and consumer

Electrical Optical Characteristics (Pulse Width:20μs, Duty: 50%)

 $T_A = 25^{\circ}C$ unless otherwise noted

| Parameter | Symbol | Min. | Тур. | Max. | Unit | Test Condition |
|-----------------------------|--------|------|------|------|-------|-----------------------------|
| Threshold Current | Ith | 4 | 8 | 12 | mA | |
| Output Power | Po | 18 | 20 | - | mW | I _f =40mA |
| Forward Voltage | Vf | 1.7 | 1.9 | 2.1 | V | I _f =40mA |
| Slope Efficiency (S.E.) | ηs | 0.45 | 0.60 | 0.75 | W/A | I _f =40mA |
| Center Wavelength | λα | 1125 | 1135 | 1145 | nm | I _f =40mA |
| Power Conversion Efficiency | PCE | 24 | | - | % | I _f =40mA |
| Wavelength Shift | Δλ/ΔΤ | - | 0.07 | - | nm/°C | I _f =40mA |
| Beam Divergence | θ | 18 | 22 | 26 | deg. | Full Width 1/e ² |

Note 1: Forward Voltage (V_i) measurement allowance is ±0.1V.

Note 2: Center Wavelength (λ_c) measurement allowance is ± 2.0 nm.

Note 3: Others measurement allowance is ±10%.

Note 4: Wafer on probe system test and chip mounted on Cu star board, and measured with operating bias current (I_f) @ 40mA @ Pulse Width (PW):20 μ s, Duty Cycle (DC): 50%.

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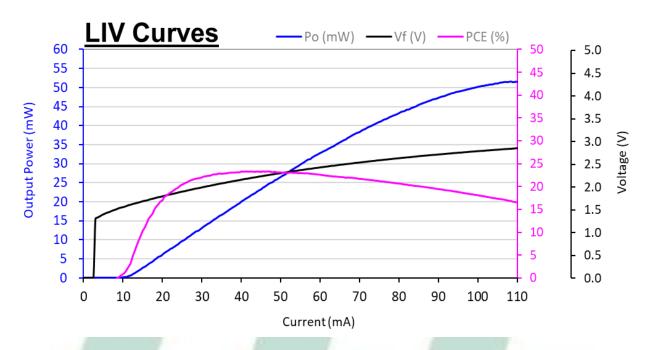
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Product :1135nm 9mil

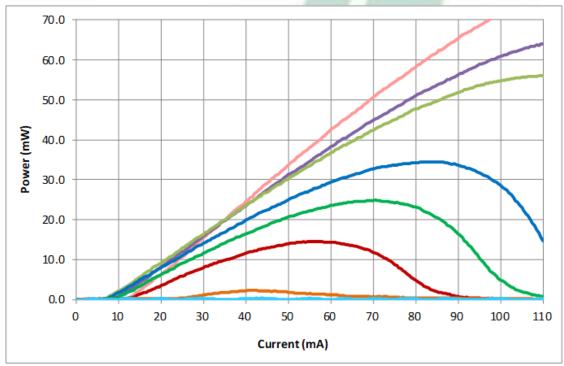
Typical Performance Curves (Pulse Width: 20μs, Duty: 50%)

■ Typical Electrical-Optical Characteristics (T_a = 25°C)



■ Typical Electrical-Optical Characteristics (T_a = -40~105°C)

3E Pulse Mode at -40°C, -20°C, 0°C, 35°C, 50°C, 65°C, 85°C, 105°C

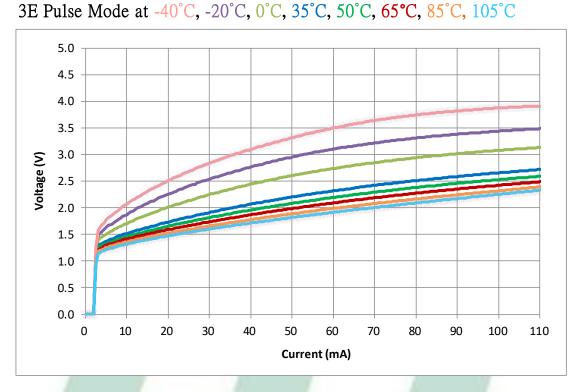


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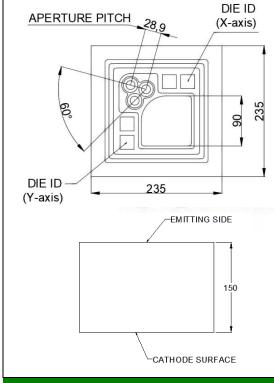
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Dimensions



| Specification | Min. | Тур. | Max. |
|----------------|------|------|---------|
| Chip width | 220 | 235 | 250 |
| Chip length | 220 | 235 | 250 |
| Chip thickness | 135 | 150 | 165 |
| Bond pad width | 1 1 | 90 | - |
| | | Ur | nit: μm |

Other Information

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RoHs Compliance:

HLJ committed to environment protection and sustainable development, this part complies with EU 2011/65/EU RoHS directive (Restrictions on the Use of Certain Hazardous Substances in Electrical and Electronic Equipment) and the relevant of held as part of our controlled documentation.

■ Packaging Q'ty:

500 ea/ die sheet, 8 die sheet/pack, 6 pack/ box, 6 box/ cargo box

■ ESD Protection:

VCSEL is very sensitive to Electrostatic discharge (ESD) and Electrical over stress (EOS), excessive ESD have damage the chip and result in performance degradation. Make sure during the whole usage and installation process that no ESD exist and electrical circuits are equipped with surge protection.

Important Notice:

The data provided in this data sheet shall be typical. In accordance with the HLJ policy of continuous improvement, specifications may change without notice.

| Revision History | | | | | | | |
|------------------|---------------------------------------|--------|-----------------|--|--|--|--|
| Revision | Description | Author | Release Date | | | | |
| 1.0 | Establish a Datasheet | Jerry | 2023/09/08 | | | | |
| 1.1 | Establish a Datasheet | Jerry | 2023/10/15 | | | | |
| 1.2 | Establish a Datasheet | Jerry | 2024/03/12 | | | | |
| 1.3 | Spec. Table adjunction (Ith. SE. PCE) | Jerry | 2024/03/20 | | | | |

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